

Comments and Corrections

Corrections to “Sharply Increased Current in Asymmetrically Aligned Polycrystalline Polymer Transistors With Sub-Domain-Size Channels”

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- [1] D. Zhang, Y. Yin, W. Lv, F. Gao, D. Pan, X. Tu, S. Ju, X. Su, X. Ma, H. Sun, Y. Xu, S. Li, and Y. Shi, “Sharply increased current in asymmetrically aligned polycrystalline polymer transistors with sub-domain-size channels,” *IEEE Electron Device Lett.*, vol. 41, no. 4, pp. 589–592, Apr. 2020, doi: [10.1109/led.2020.2976653](https://doi.org/10.1109/led.2020.2976653).

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